

Epitaxial van der Waals heterostructures of Cr_2Te_3 on 2D materials

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Achieving large-scale growth of two-dimensional (2D) ferromagnetic materials with high Curie temperature (T_C) and perpendicular magnetic anisotropy (PMA) is highly desirable for the development of ultra-compact magnetic sensors and magnetic memories. In this context, van der Waals (vdW) Cr_2Te_3 appears as a promising candidate. Bulk Cr_2Te_3 exhibits strong PMA and a T_C of 180 K. Moreover, both PMA and T_C might be adjusted in ultrathin films by engineering composition, strain, or applying an electric field. In this work, we demonstrate the molecular beam epitaxy (MBE) growth of vdW heterostructures of five-monolayer quasi-freestanding Cr_2Te_3 on three classes of 2D materials: graphene (semimetal), WSe_2 (semiconductor) and Bi_2Te_3 (topological insulator). By combining structural and chemical analysis down to the atomic level with *ab initio* calculations, we confirm the single crystalline character of Cr_2Te_3 films on the 2D materials with sharp vdW interfaces. They all exhibit PMA and T_C close to the bulk Cr_2Te_3 value of 180 K. *Ab initio* calculations confirm this PMA and show how its strength depends on strain. Finally, Hall measurements reveal a strong anomalous Hall effect, which changes sign at a given temperature. We theoretically explain this effect by a sign change of the Berry phase close to the Fermi level. This transition temperature depends on the 2D material in proximity, notably as a consequence of charge transfer. MBE-grown Cr_2Te_3 /2D material bilayers constitute model systems for the further development of spintronic devices combining PMA, large spin-orbit coupling and sharp vdW interface.

I. INTRODUCTION

The discovery of ferromagnetic order in two-dimensional (2D) materials like $\text{Cr}_2\text{Ge}_2\text{Te}_6$ [1] and CrI_3 [2] has paved the way for the development of new van der Waals (vdW) heterostructures [3]. Combined with the large spin-orbit coupling and low crystal symmetries of 2D materials like transition metal dichalcogenides (TMD) [4], 2D ferromagnets represent a key ingredient to construct ultra-compact devices for spintronic applications [5] such as spin transfer torque (STT) or spin-orbit torque (SOT) magnetic random access memories (MRAMs). These technologies based on 2D materials would allow for the miniaturization of today's devices as well as a sizeable reduction of energy consumption [6].

For this purpose, 2D ferromagnets with Curie temperatures (T_C) higher than room temperature and with perpendicular magnetic anisotropy (PMA) are required [7]. Fe_xGeTe_2 ($x=3, 4$ or 5) [8] and $\text{Cr}_{1+\delta}\text{Te}_2$ ($0 \leq \delta \leq 1$) [6-19] have emerged recently as the two most promising families of materials to achieve such conditions. $\text{Cr}_{1+\delta}\text{Te}_2$

materials are composed of 1T- CrTe_2 monolayers (ML) separated by a variable amount of intercalated chromium atoms (from empty to fully occupied). CrTe_2 is a vdW ferromagnet with room temperature ferromagnetic order ($T_C = 315$ K) [9–11], whereas $\text{Cr}_{1+\delta}\text{Te}_2$ ($\delta > 0$) are quasi vdW ferromagnets with T_C ranging from 160 K to 350 K and varying magnetic anisotropy from out-of-plane to in-plane easy axis of magnetization [9-14]. Magnetic properties of $\text{Cr}_{1+\delta}\text{Te}_2$ have been shown to depend on its stoichiometry [12, 13], its thickness in case of thin films [14], the Cr-Te flux ratio during crystal growth [15] and strain in the layer [16, 17]. The stoichiometry of the stack could be adjusted by post-growth annealing [12] or by changing elemental fluxes [18]. Highly efficient control of magnetic properties is required for spintronic applications [5] and it is, therefore, necessary to understand the growth mechanisms of these materials, especially for the development of functional vdW heterostructures. Exotic topological phenomena such as the topological Hall effect have also been reported in $\text{Cr}_2\text{Te}_3/\text{Bi}_2\text{Te}_3$ bilayers [19, 20] or $\text{Cr}_2\text{Te}_3/\text{Cr}_2\text{Se}_3$ [21]. Moreover, non-collinear spin textures were shown in Cr_2Te_3 as a consequence of anti-ferromagnetic coupling between neighboring chromium atoms [22] making it an interesting host for exotic, trivial or topological spin textures.

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In this work, we report the vdW epitaxy [23, 24] of 5 ML of Cr_2Te_3 on three different 2D materials, namely graphene (a semimetal with exceptional electronic properties), WSe_2 (a transition metal dichalcogenide semiconductor exhibiting strong photo-luminescence and spin-valley locking in its monolayer form), and Bi_2Te_3 (a topological insulator with strong spin-orbit interaction). Particular care was given to their full structural and magnetic characterizations including the determination of the film stoichiometry. Those bilayers represent model systems to study proximity effects in vdW heterostructures, interface spin textures as well as spin-orbit torques. The Cr_2Te_3 films were grown by molecular beam epitaxy (MBE) in ultrahigh vacuum (UHV) by depositing simultaneously Cr and Te atoms. They exhibit in-plane compression and out-of-plane expansion with respect to the bulk phase. This strain is shown to vary with the post-growth annealing, but it is almost independent of the 2D layer underneath. Indeed, Cr_2Te_3 films on graphene and WSe_2 annealed at 400°C show the same lattice parameters, which are equal to the ones of 5 ML free-standing Cr_2Te_3 calculated by *ab initio* methods. This demonstrates that the vdW epitaxy of Cr_2Te_3 on 2D materials leads, after annealing, to the formation of quasi-freestanding films with negligible interaction with the substrate. We then correlate the PMA of Cr_2Te_3 with strain and confirm our experimental findings using *ab initio* calculations. Finally, magnetotransport measurements reveal a change of sign of the anomalous Hall effect in Cr_2Te_3 with temperature and point out a charge transfer from the substrate to the film changing the p-type doping level of Cr_2Te_3 . This effect has already been observed in several vdW heterostructures [25, 26]. The charge transfer is shown to govern the temperature at which the anomalous Hall effect changes sign. We reproduce theoretically this effect by showing a sign change of the Berry phase close to the Fermi level. Finally, our work demonstrates the ability of MBE to synthesize model vdW heterostructures incorporating 2D materials and quasi vdW ferromagnets which are highly promising for future 2D-based spintronic devices.

II. METHODS

A. Experimental methods

All the films were grown by MBE using a home-designed UHV system. Metallic elements (Cr, W, Bi and Al) were evaporated using an electron gun and the growth rate was controlled using a quartz microbalance, whereas chalcogens (Te, Se) were evaporated from Knudsen cells. Their elemental fluxes were measured by a pressure gauge. The substrates were attached to a molybloc by wetting In underneath. The temperature of the samples during growth was controlled by a thermocouple touching the backside of the molybloc. Scanning transmission electron microscopy (STEM) mea-

surements were performed using a Cs-corrected FEI Themis at 200 kV. HAADF-STEM (high-angle annular dark field) images were acquired using a convergence angle of 20 mrad and collecting electrons scattered at angles higher than 60 mrad. STEM specimens were prepared by the focused ion beam (FIB) lift-out technique using Zeiss Crossbeam 550. The sample was coated with protective carbon and platinum layers prior to the FIB cut.

The out-of-plane x-ray diffraction (XRD) measurements were performed using a Panalytical Empyrean diffractometer operated at 35 kV and 50 mA, with a cobalt source, ($K\alpha = 1.79 \text{ \AA}$). A PIXcel-3D detector allowed a resolution of 0.02° per pixel, in combination with a divergence slit of 0.125° on the source side. Grazing in-plane XRD measurements were performed with a SmartLab Rigaku diffractometer equipped with a copper rotating anode ($K\alpha = 1.54 \text{ \AA}$) operating at 45 kV and 200 mA. Collimators with a resolution of 0.5° were used both on the source and the detector sides. The grazing incidence close to the critical angle of the substrate was optimized to maximize the intensity of the Cr_2Te_3 Bragg peaks. Both diffractometers were equipped with multi-layer mirrors on the source side and $K\beta$ filter on the detector side. Raman measurements were performed with a Horiba Raman setup with a 632 nm laser excitation source and a spot size of $0.5 \mu\text{m}$. The signal was collected by using a 1800 grooves/mm grating.

Rutherford backscattering (RBS) measurements were performed with a $^4\text{He}^+$ beam delivered by the SAFIR Platform at Sorbonne University in Paris at beam energies ranging from 1.5 to 2.0 MeV. For all samples, the scattering angle was set to 160° and the resolution of the detector was 13.5 keV. To avoid channeling effects, the samples were tilted with respect to the normal of the sample in two perpendicular directions.

The magnetic properties were measured by superconducting quantum interference device (SQUID) magnetometry with the magnetic field applied parallel or perpendicular to the film plane. The measurements were performed using a Quantum Design magnetic property measurement system. The diamagnetic contribution was subtracted using the data at high field ($\geq 3\text{T}$) and some parasitic contributions were corrected by subtracting signals measured well above the T_C of the systems (at 350K). This method has already been used successfully by Ribeiro *et al.* [8] and confirmed by comparing it with magnetic moments extracted from x-ray magnetic circular dichroism (XMCD) measurements.

The XMCD measurements were performed on the DEIMOS beamline [27] of synchrotron SOLEIL (Saint Aubin, France). The signals were recorded using the Total Electron Yield (TEY) method. Each XMCD spectrum was obtained from four measurements, where both the circular helicity and the direction of the applied magnetic field were flipped. The XAS data are then averaged (the signals of opposite helicity and field) and normalized to the absorption at the pre-edge of chromium (565 eV). The XMCD spectra are normalized to their maximum

for comparison.

In order to carry out magnetotransport measurements, we processed Hall bars out of Cr_2Te_3 films by laser lithography and argon etching. Electrical contacts were made of e-beam evaporated $\text{Ti}(10\text{ nm})/\text{Au}(100\text{ nm})$ bilayers. The length and width of Hall bars were approximately $100\text{ }\mu\text{m}$ and $10\text{ }\mu\text{m}$ respectively. All the electrical measurements were performed using an OXFORD Spectromag setup working in the 1.6-300 K temperature range with magnetic fields up to 7 Tesla. The anomalous Hall contribution was obtained by fitting the experimental data with a hyperbolic tangent function.

B. Calculation methods

The *ab initio* calculations were performed using density functional theory (DFT) as implemented in the Vienna *ab initio* simulation package (VASP) [28, 29] with the generalized gradient approximation (GGA) pseudopotentials in the Perdew-Burke-Ernzerhof (PBE) parametrization [30]. The DFT+ U approach using Dudarev's formulation [31] was applied with an effective Hubbard correction $U_{\text{eff}} = 2.1\text{ eV}$ to localize the Cr d -orbitals. A Cr pseudopotential with semicore p electrons was chosen and an energy cutoff of 330 eV was used for the plane-wave basis. The van der Waals interaction was approximated by the DFT-D3 method [32] with the Becke-Johnson damping [33].

To compute the relaxed heterostructures of Cr_2Te_3 with 2D materials, the relative orientation of the two materials in the calculation was not taken from an experiment, but chosen in a systematic way [34] to minimize the lattice mismatch. This captures more realistically the weak epitaxy of the heterostructure.

The magnetic anisotropy calculation procedure is described in [35]. A $9\times 9\times 5$ k-point mesh was found to be sufficient. The volume was fixed at its calculated equilibrium bulk value, while the in-plane and out-of-plane lattice parameters (a and c) were varied. A demagnetizing energy contribution $E_{\text{demag}} = -\mu_0 M_s^2/2$ was added to the calculated magnetocrystalline energy, using the experimental M_s value $\approx 300\text{ kA/m}$.

The anomalous Hall effect was computed [36] by constructing a tight-binding Hamiltonian based on maximally localized Wannier functions using the Wannier90 package [37]. We verified carefully that the model reproduces well the band structure of Cr_2Te_3 from the original DFT calculation. Using the WannierBerri package [38, 39], the Berry curvature was then calculated for a dense k-point mesh and integrated over the Brillouin zone to obtain the Berry phase, proportional to the anomalous Hall conductivity, at various Fermi level positions.

III. SAMPLE PREPARATION

In this study, we have grown samples of 5 layers of Cr_2Te_3 corresponding to a thickness of 6.1 nm on three different vdW surfaces: 1 monolayer of WSe_2 deposited on GaAs, 10 layers of Bi_2Te_3 on Al_2O_3 , which were both grown in situ by MBE and monolayer graphene, which was obtained by the controlled graphitization of 4H-SiC(0001) [40] in another reactor.

WSe_2 was grown epitaxially on Se-passivated GaAs(111)B as detailed in [41]. Bi_2Te_3 was grown epitaxially on sapphire. For this purpose, sapphire substrates were first annealed in air for one hour at 1000°C with a heating ramp of 40 minutes starting from room temperature. They were additionally annealed in situ for 30 minutes at 800°C . 10 quintuple layers of Bi_2Te_3 were then grown by co-evaporating Bi and Te from an electron gun and a cracker cell at deposition rates of 0.057 and $0.1\text{ }\text{\AA}/\text{s}$, respectively. The substrate temperature was maintained at 250°C during the growth. Post-growth annealing at 300°C under Te flux was done for 10 minutes to improve the crystal quality. Finally, Gr/SiC layers were annealed in situ for 30 minutes at 650°C after their transfer.

The Cr_2Te_3 films were grown using a two-step process as sketched in Fig. 1(a). The growth temperature, Te:Cr ratio and deposition rate were set at 300°C , 10, and 0.25 L/min respectively. The Te cell shutter was opened 1 minute before chromium deposition to ensure that the surface of the substrate was saturated in Te at the first stage of growth [see Fig. 1(a)]. After the growth, the samples were annealed at 400°C for 10 minutes using the same Te flux as during the growth and a heating ramp of 40°C/min . The samples were then cooled down to 50°C and 3 nm of aluminum was deposited to prevent oxidation of the layers during transfers between experimental setups.

The film morphology was monitored in situ by reflection high-energy electron diffraction (RHEED) as can be seen in Fig. 1(b) in the case of WSe_2 . A streaky diffraction pattern was observed indicating a flat and well-crystallized surface. The different diffraction patterns along the two high symmetry axes of the WSe_2 substrate [Fig. 1(c)-(e)] indicate a good alignment of Cr_2Te_3 grains with the underlying layer. After annealing, the width of the diffraction rods is approximately divided by 2 as a consequence of the larger grain size [Fig. 1(d)-(f)]. We made similar RHEED observations for the two other vdW substrates Bi_2Te_3 and graphene (see the Supplemental Material Fig. S1), except an increased isotropic contribution on graphene attributed to a lower interaction with the substrate.

IV. STRUCTURAL PROPERTIES

We found similar structural characteristics for Cr_2Te_3 grown on WSe_2 and graphene. Therefore, we present the

results of the growth on WSe₂ and the ones on graphene are given in the Supplemental Material. The results on Bi₂Te₃ are shown in Fig. 5.

Figure 2(a) is a cross-section STEM image of the layers, revealing a sharp and well-defined interface between the vdW ferromagnet and the 2D layer as evidenced by the W-Te distance between W atoms of WSe₂ and the first Te atoms plane of Cr₂Te₃ with a value of 5.3 Å. This value is taken to obtain a better experimental determination of the gap (due to the large atomic number of W with respect to Se) as can be seen in Fig. 2(b) showing a line profile along the c-direction of the heterostructure. This corresponds to a vdW gap Δ_{vdW} of 3.5 Å if we assume a relaxed WSe₂ layer, in agreement with our XRD data (see Fig. 3). It is worth noting that we resolve an intensity difference between fully and partially filled Cr planes. Indeed, every two Cr planes, only one third of the lattice sites are occupied by intercalated Cr atoms in the case of Cr₂Te₃. We also observe that the monolayer of WSe₂ remains intact after the growth of Cr₂Te₃ on top.

The experimental W-Te distance was compared with the one obtained by *ab initio* calculations performed on Cr₂Te₃/WSe₂ consisting of 1.5 unit cell thick Cr₂Te₃ on top of a single layer of WSe₂ [see Fig. 2(c)]. The calculated distance is 5.08 Å, in good agreement with the experimental one of 5.3 Å.

To accurately determine the lattice parameters of Cr₂Te₃ layers and crystal orientation with respect to each of the substrates, systematic XRD analysis were performed to extract the in-plane and out-of-plane lattice parameters. These measurements allowed us to measure accurately the strain in each layer when compared with the bulk lattice parameters.

Figure 3(a), 3(b) and 3(c) show XRD out-of-plane, in-plane radial and in-plane azimuthal scans of Cr₂Te₃/WSe₂/GaAs (sample 2, see Table I) respectively. The diffraction patterns of Cr₂Te₃ deposited on WSe₂ reveal the single crystalline character of the film and the clear epitaxial relationship with WSe₂. The thin Bragg peaks in radial scans in Fig. 3(b) (Full Widths at Half Maximum -FWHM- of 0.48° and 0.70°) indicate the large grain size and the uniformity of the lattice parameter. In Fig. 3(c), the mosaic spread (FWHM of 1.54°) is negligibly small which confirms the perfect orientation of Cr₂Te₃ on WSe₂.

All the XRD data are summarized in Table I. Compared to bulk values of Cr₂Te₃ with $a = 6.812$ Å and $c = 12.07$ Å [42], we systematically found an in-plane compressive strain and a resulting out-of-plane expansion. We found similar lattice parameters regardless of the substrate underneath although the mismatch between inter-atomic distances is very large (WSe₂:+19.1%/Gr:+56.3%/Bi₂Te₃:-10.8%). An in-plane compressive strain would be expected for Cr₂Te₃ deposited on WSe₂ and graphene, whereas an in-plane

tensile strain would be expected for the growth on Bi₂Te₃. Moreover, we could not find any commensurable relationship between the in-plane lattice parameter of Cr₂Te₃ and the one of the substrate. This was confirmed by *ab initio* calculations: the lattice parameter of the vdW heterostructure corresponds to the one of bulk Cr₂Te₃ above 7 MLs of Cr₂Te₃, as demonstrated for Cr₂Te₃/Gr (see the Supplemental Material Fig. S2). We thus conclude about the pure vdW interaction between Cr₂Te₃ and the substrate. The slight difference between lattice parameters might be due to the surface topography (presence of steps, terrace, etc.) and the microscopic structure of Cr₂Te₃ (grain size, grain boundaries, etc.). However, the energy given to the system by annealing seems to be the driving force to control the final crystal structure since all the lattice parameters converge to the same values after annealing at 400°C. Besides, layers grown on graphene exhibit a much larger mosaic spread even after annealing, indicating even lower interaction between Cr₂Te₃ and the substrate during growth.

The measured lattice parameters match well with the *ab initio* calculations performed on ~ 5 nm-thick free-standing films which corresponds to the experimental thickness (see Fig. 4). In particular, for the Cr₂Te₃ films annealed on graphene and WSe₂ (samples 2 and 4), the experimental lattice parameters fall exactly on the theoretical curve confirming a weak interaction between the film and the substrate. The case of Cr₂Te₃ grown on Bi₂Te₃ is discussed later in Fig. 5.

In Table I, we also show the measured composition of some selected samples by RBS (see the Supplemental Material Fig. S4) and found compositions very close to Cr₂Te₃. No measurement could be performed on GaAs substrates as Ga and As are heavier than chromium, causing the Cr signal peak to lie in the substrate background, preventing any determination of the Cr:Te ratio in these samples.

Raman spectroscopy was also performed before and after the growth of Cr₂Te₃ to control the quality and integrity of the 2D layers. Figure 3(d) depicts the Raman spectra of WSe₂/GaAs and Cr₂Te₃/WSe₂/GaAs. The width and position of WSe₂ peaks are preserved, indicating that the deposition of Cr₂Te₃ did not alter the WSe₂ layer. The reference signal of WSe₂/GaAs (green curve) was measured with a 532 nm laser instead of 633 nm as the other samples, explaining the intensity differences. Similar observations have been made on the Cr₂Te₃/graphene heterostructure as shown in the Supplemental Material Fig. S5.

Figure 5(a) shows the Raman spectra of Cr₂Te₃/Bi₂Te₃/Al₂O₃ at different stages of growth. We detected two characteristic peaks of Bi₂Te₃ at 101.8 cm⁻¹ and 133.5 cm⁻¹, which correspond to the E_g^2 and A_{1g}^2 vibrational modes and have also been reported in [43]. After the deposition of 5 layers of Cr₂Te₃ at 300°C, those peaks remained unchanged (the amplitude drop is explained by the partial absorption of the laser

fluence in the metallic Cr_2Te_3 layer). However, when the sample was annealed at 400°C , the two characteristic peaks of Bi_2Te_3 disappeared. Indeed, x-ray diffraction measurements performed before and after annealing in Fig. 5(b) clearly show the disappearance of Bi_2Te_3 after thermal annealing. Finally, in Fig. 5(c), RBS measurements on the annealed sample show the absence of Bi in the heterostructure. This reveals that Bi_2Te_3 was evaporated during annealing leaving the Cr_2Te_3 film on the pristine sapphire substrate. We shaded the structural data of this sample (n°6) in Table I because Cr_2Te_3 is standing directly on the sapphire substrate after annealing. Moreover, in this case, the substrate is no more vdW and defects might have been created in Cr_2Te_3 by evaporation of the Bi_2Te_3 layer underneath.

V. MAGNETIC PROPERTIES

Hysteresis loops were measured by SQUID magnetometry at 5 K and are displayed in Fig. 6. For all samples, the easy axis of magnetization was found along the c -axis and by integrating the difference of area between the out-of-plane and the in-plane magnetization curves, the magnetic anisotropy energy (MAE) could be experimentally derived for all the samples.

The origin of ferromagnetism in our layers was confirmed by XMCD performed at the SOLEIL synchrotron radiation source. The energy spectra are shown in Fig. 7 and a hysteresis loop is displayed in the Supplemental Material Fig. S6. A clear magnetic dichroism signal with a similar spectral shape was obtained for all the three different substrates. This proves that the chemical environment of Cr atoms in Cr_2Te_3 films is essentially independent of the substrate. The lower magnetic moment for the sample on $\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$ [Fig. 7(c)] is explained by a lower sample thickness (three monolayers instead of five).

To better understand the magnetic properties, the magnetic anisotropy energy was calculated theoretically as a function of strain for bulk Cr_2Te_3 and was compared to experimental values in Fig. 8. The results reveal that the MAE is correlated to the strain of the layers. Overall, the trend and magnitude correspond well with experimental data. In particular, there is no sharp discontinuous change from positive to negative anisotropy values, as reported in [14]. However, the experimental data show larger PMA values compared to the theory. Since our calculations were performed in bulk Cr_2Te_3 , we can attribute this shift to the presence of interfacial PMA at the Cr_2Te_3 /substrate or $\text{Cr}_2\text{Te}_3/\text{AlO}_x$ capping layer interfaces.

To determine the T_C of each annealed sample, we recorded the remanent magnetization after saturation at 5 T (with 5 K steps and no external field) as a function of temperature (Fig. 9). A value close to 180 K was found for the three substrates demonstrating again the

very weak interaction between Cr_2Te_3 and the vdW substrates. Here, we believe that the T_C is fully determined by the 2:3 stoichiometry of the films.

VI. MAGNETOTRANSPORT

To study the magnetotransport properties, we performed four-probe resistance measurements and found an increasing longitudinal resistivity of Cr_2Te_3 layers with temperature indicating a metallic character (see the Supplemental Material Fig. S8). The resistivity is of the order of $500 \mu\Omega\cdot\text{cm}$ at 4 K. Figure 10(a) shows the Hall resistivity of 5 ML of Cr_2Te_3 deposited on WSe_2 (sample 2) as a function of the perpendicular magnetic field at different temperatures. For visibility, the ordinary Hall slope was subtracted and a carrier density of 1.6×10^{15} holes/ cm^2 was extracted at 50 K, compared to 7.0×10^{15} holes/ cm^2 for 5 ML of Cr_2Te_3 directly deposited on sapphire (see the Supplemental Material Fig. S9), indicating a charge transfer from the WSe_2 layer. The clear anomalous Hall signal confirmed the strong PMA of the ferromagnet.

The same measurements were performed for a sample grown on Bi_2Te_3 (sample 6) and annealed at 400°C (resulting in Bi_2Te_3 evaporation), as shown in Fig. 10(b). The ordinary hall slope was removed and a carrier density of 4.5×10^{15} holes/ cm^2 was extracted at 50 K. Since there is no charge transfer with sapphire, the difference in carrier density with Cr_2Te_3 directly grown on sapphire could be explained by the presence of defects at the interface introduced during the evaporation of the Bi_2Te_3 layer.

In Fig. 11(a), the anomalous Hall resistivity is extracted for the two samples on sapphire as a function of temperature. We observe in both cases a sign change of the anomalous Hall resistivity below the Curie temperature of 180 K. Similar observations were reported in [44, 45]. The possible origin of this effect is discussed in the following as a consequence of the energy-dependent Berry phase of Cr_2Te_3 .

In the temperature range of the AH resistivity sign reversal, a resonance of the Hall signal manifested as peaks at the coercive fields can be observed. Figure 11(b) shows the Hall resistivity after subtraction of the ordinary and anomalous Hall effect at two temperatures below the sign change and one above. The bumps are enhanced when the temperature is closer (but still lower) than the temperature of the sign change and disappear above it. The width of the bumps also decreases with temperature, which could be related to the shrinking of the coercive field. The physical origin of such an effect is still under debate. In a similar heterostructure, Chen *et al.* [19] interpreted it as the topological Hall effect, which would originate from the presence of magnetic skyrmions. Skyrmions nucleate during the magnetization reversal and give rise to an extra transverse transport

channel inducing a peak in the Hall resistivity. Imaging such spin textures has been performed by Lorentz-TEM in Cr_3Te_4 layers [46]. Nevertheless, another explanation has been put forward by other groups as two anomalous Hall contributions with opposite signs [47]. The origin could be thickness variations, inhomogeneities in the film or interface effects leading to the sign of the AHE being different [48, 49]. In the case of Cr_2Te_3 these peaks appear close to the anomalous Hall resistivity sign change. If the thickness of the layer is not strictly constant over the Hall bar, some areas could have slightly different temperatures at which the anomalous Hall signal changes sign. In this case, for intermediate temperatures, two AHE components with opposite signs would indeed add up and could explain the observed behavior.

The sign reversal of the anomalous Hall effect observed experimentally can be elucidated by *ab initio* calculations. The longitudinal resistivity is in the range where the contribution to AHE from intrinsic and impurity scattering components coexist, while the intrinsic part stays significant [45]. We thus calculated the intrinsic contribution to AHE for bulk Cr_2Te_3 (see Methods). As shown in Fig. 12, it exhibits a clear sign reversal very close to E_F (~ -10 meV). This is in contrast with previous calculations [21] where the sign reversal occurs 330 meV above E_F . This difference is due to the inclusion of the vdW corrections in our DFT calculations (see the Supplemental Material Fig. S10). We consider three different mechanisms influencing the value and sign of the anomalous Hall conductivity: (a) thermal broadening around the Fermi level (of the order of $k_B T$, i.e., 15 meV for $\Delta T = 180$ K), (b) charge transfer with the substrate (which we calculated was greatest on graphene inducing a Fermi level shift of $\approx +50$ meV), and (c) out-of-plane strain (see the Supplemental Material Fig. S11). All these effects change the system energy in a range compatible with the calculations in Fig. 12.

We believe that the strain dependence of $\sigma_{\text{AH}}^{\text{int.}}$ is at the origin of the change of sign of the AHE reported in Fig. 11(a). Anisotropic lattice expansion with temperature was reported for $\text{Cr}_{1+\delta}\text{Te}_2$ [50], which directly affects the AHE conductivity. To illustrate this qualitative argument, we chose in Fig. 12 two reasonable strain values in agreement with the structural data we obtained, keeping in mind that films in this work have c/a ranging between 1.797 and 1.868 (see Fig. 8). If the Fermi level of the sample lies in the red shaded area (between -8 and 0 meV), the evolution of c/a from 1.79 to 1.82 with temperature would lead to a sign change of $\sigma_{\text{AH}}^{\text{int.}}$.

Another effect that could influence this picture is the thermal broadening of the Fermi-Dirac distribution upon heating. However, we obtained a mostly linear dependence of $\sigma_{\text{AH}}^{\text{int.}}$ on energy close to the Fermi level. When considering contributions above and below E_F , both would cancel out as the thermal broadening is symmetric. Finally, the role of the substrate has to be also accounted for. As shown experimentally, charge transfer with the 2D materials was observed and leads to a shift

of the Fermi level. This explains why the effect is present for samples standing on sapphire and not for the one on WSe_2 . Indeed, for sapphire, the Fermi level is the lowest (carrier density of 4.5×10^{15} holes/cm² and 7.0×10^{15} holes/cm²) so that we observe a sign change whereas the Fermi level is shifted up for WSe_2 (1.6×10^{15} holes/cm²) and the sign change is absent. This observation is in agreement with the fact that the sign change in *ab initio* calculations occurs for lower energies as shown in Fig. 12.

Finally, in Fig. 13, we present magnetotransport measurements on 5 layers of Cr_2Te_3 grown on graphene/SiC (sample 3). Both layers are metallic and contribute to conduction. The Hall resistivity is plotted as a function of the applied perpendicular magnetic field at different temperatures. No anomalous Hall resistivity sign change is measurable below the Curie temperature. This observation is in good agreement with *ab initio* calculations since the extracted carrier density at 50 K, which is the lowest: 1.4×10^{14} holes/cm², corresponds to a Fermi level position shifted towards higher values. On top of the anomalous Hall contribution following the magnetization reversal at 0.5 T (at 50 K), another step close to 0.4 T is also present. This two-step signal behavior (absent in SQUID and XMCD measurements) vanishes progressively when increasing the temperature and disappears around 100 K, well below the Curie temperature. The origin of this effect needs further investigation and is out of the scope of the present work.

VII. CONCLUSION

In conclusion, we reported the vdW epitaxy of Cr_2Te_3 on three different 2D materials. We revealed the pristine interface and the preservation of the intrinsic properties of the underlying layers after the growth of the vdW ferromagnet. We demonstrated the free-standing character of Cr_2Te_3 layers grown on these 2D materials after an annealing step at 400°C. Besides, the energy given to the system during the growth was identified as a way to control the crystal structure and tune the magnetic properties. We observed a correlation between the PMA energy of the system and the lattice parameters which was elucidated by *ab initio* calculations. Finally, we theoretically predicted a strain-sensitive sign change of the Berry phase very close to the Fermi level explaining the measured sign change of AHE with temperature. Charge transfer between the 2D layers and Cr_2Te_3 was shown to directly affect the temperature at which the AHE changes sign by shifting the Fermi level. To summarize, this system outputs highly tunable structural, magnetic and electrical properties, which presents an important asset for future spintronic applications.

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Equipex+ project 2D-MAG on two-dimensional magnetic materials. We acknowledge the financial support from the ANR project ELMAX (ANR-20-CE24-0015) and from the LANEF framework (ANR-10-LABX-51-01) for its support with mutualized infrastructure. This work was partly supported by the French RENATECH network. XMCD experiments were performed on the DEIMOS beamline at SOLEIL Synchrotron, France (proposal number 20220542). We are grateful to the SOLEIL staff for smoothly running the facility.

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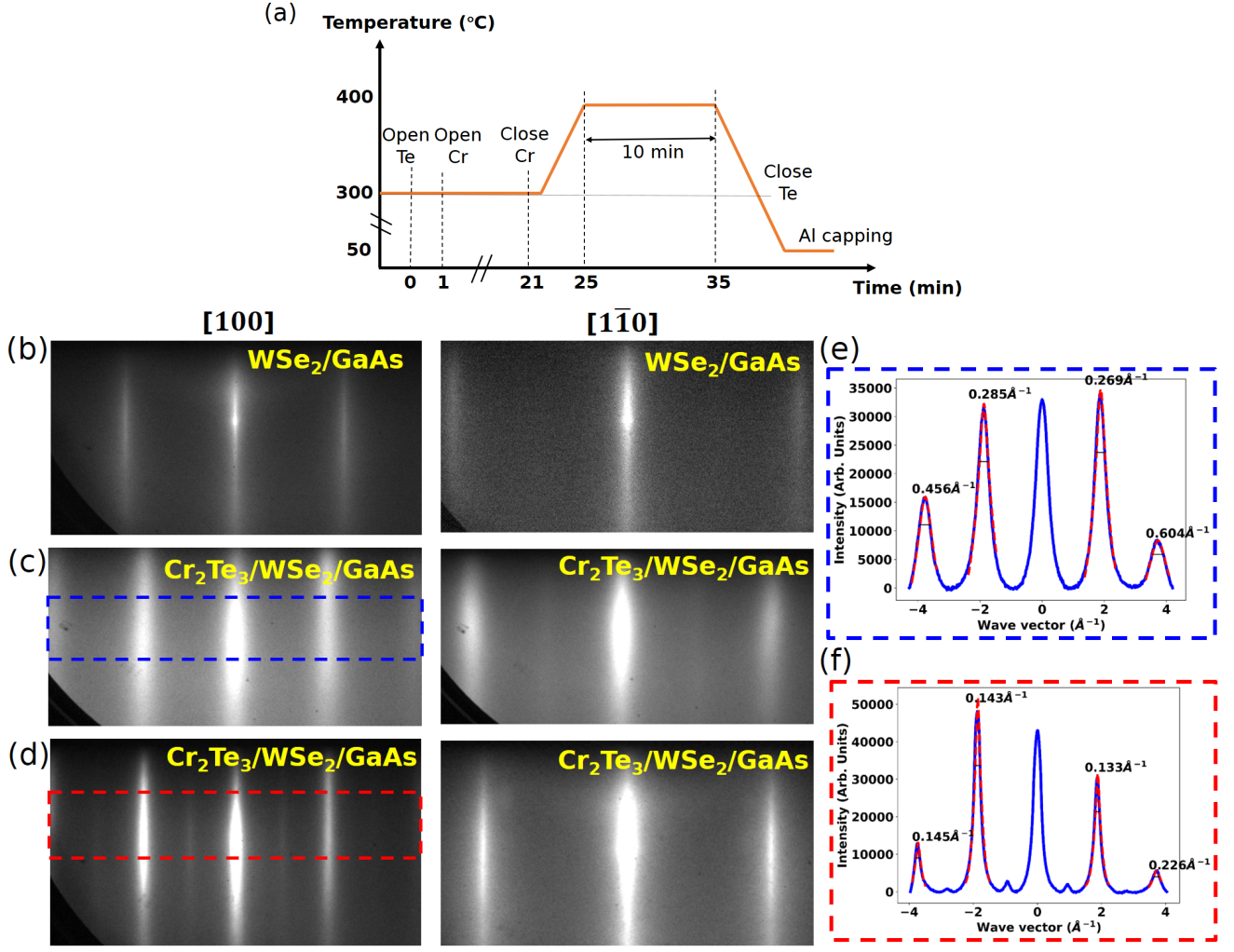


FIG. 1: MBE growth of Cr₂Te₃ on the 2D transition metal dichalcogenide WSe₂. (a) Sketch of the deposition procedure. The growth temperature was 300°C and in situ annealing was performed at 400°C. (b) in situ RHEED images of 1 layer WSe₂ deposited on GaAs(111)B along two crystal directions (Time = 0 min). (c) RHEED pattern after the deposition of Cr₂Te₃ (Time = 21 min). (d) RHEED pattern after annealing (Time = 35 min). (e,f) Intensity profiles of the RHEED diffraction pattern for images c (blue dashed box) and d (red dashed box) respectively.

N°	2D layer	Temperature	a (Å)	$\frac{a-a_{\text{bulk}}}{a_{\text{bulk}}}$	c (Å)	$\frac{c-c_{\text{bulk}}}{c_{\text{bulk}}}$	$\frac{c}{a}$	$\Delta\theta_{//}$	$\Delta\phi$	Stoichiometry
1	WSe ₂	300°C	6.731	-1.2%	12.44	+3.1%	1.848	1.00°	2.36°	
2	WSe ₂	400°C	6.760	-0.76%	12.28	+1.7%	1.817	0.62°	1.54°	
3	graphene	300°C	6.754	-0.88%	12.18	+0.91%	1.804	0.72°	24.8°	Cr _{1.88} Te ₃
4	graphene	400°C	6.758	-0.79%	12.30	+1.9%	1.820	0.60°	16.6°	
5	Bi ₂ Te ₃	300°C	6.691	-1.8%	12.50	+3.6%	1.868	0.87°	2.77°	Cr _{1.97} Te ₃
6	Bi ₂ Te ₃	400°C	6.778	-0.50%	12.18	+0.91%	1.797	0.56°	1.28°	Cr _{2.07} Te ₃

TABLE I: Growth/annealing temperature and structural parameters measured by x-ray diffraction and chemical composition from RBS, with a (c) the in-plane (out-of-plane) lattice parameter, the radial width ($\Delta\theta_{//}$) of the (300) diffraction peak and the mosaic spread ($\Delta\phi$) measured on the same Bragg peak.

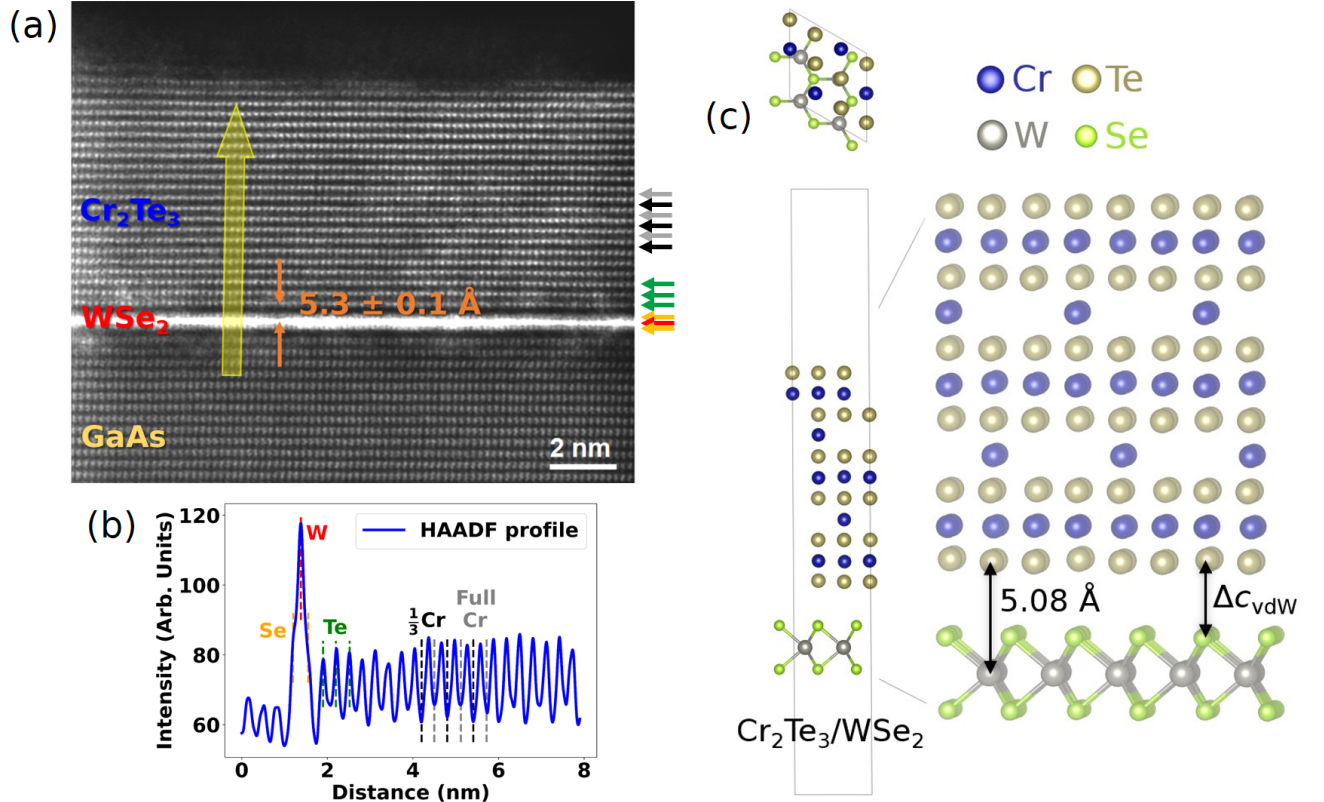


FIG. 2: (a) Low-pass filtered HAADF-STEM image of 5 layers Cr_2Te_3 grown on one monolayer WSe_2 deposited on a $\text{GaAs}(111)\text{B}$ surface. The van der Waals gap between the layers is shown to highlight the high quality of the interface. Arrows on the right side indicate the position of the atomic planes noted in the line profile. (b) Line profile along the c -direction of Cr_2Te_3 layers (yellow arrow) with intensity distinction between partially and fully occupied Cr planes [see crystal structure in (c)]. (c) A unit cell of the calculated $\text{Cr}_2\text{Te}_3/\text{WSe}_2$ heterostructure - in the interstitial planes, only $1/3$ of the lattice sites is occupied by the intercalated Cr atoms. The *ab initio*-calculated W-Te distance is 5.08 Å.

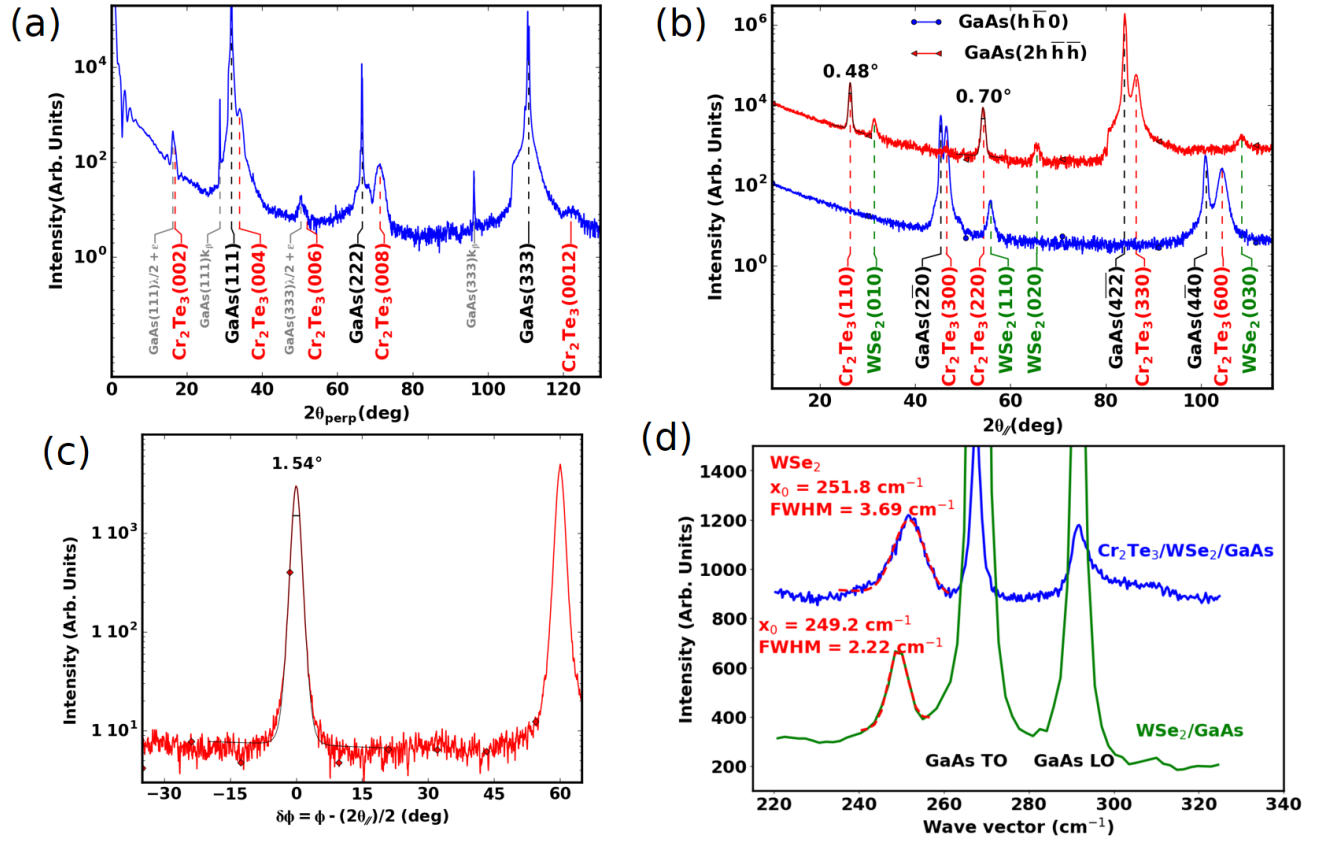


FIG. 3: Post-growth characterization of the crystal structure of Cr₂Te₃/WSe₂/GaAs (sample 2). (a) Out-of-plane $\Theta/2\Theta$ XRD scan shows, in addition to Cr₂Te₃ (00l) peaks (red), GaAs substrate peaks (black) with weak additional peaks due to spurious radiations not completely eliminated by the mirror and the K β filter (grey). (b) In-plane radial XRD scans performed along the GaAs substrate $R=(hh0)$ direction, and $R+30^\circ=(2h\bar{h}h)$ direction. These scans show the substrate peaks (black), WSe₂ (green), and Cr₂Te₃ peaks (red) labeled with their FWHM. (c) In-plane azimuthal XRD scan of the (300) peak measured within a range of 100° shows thin peaks with a FWHM of 1.54° separated by 60° corresponding to the 6-fold symmetry of the crystal. (d) Raman spectra of WSe₂ before and after deposition of Cr₂Te₃.

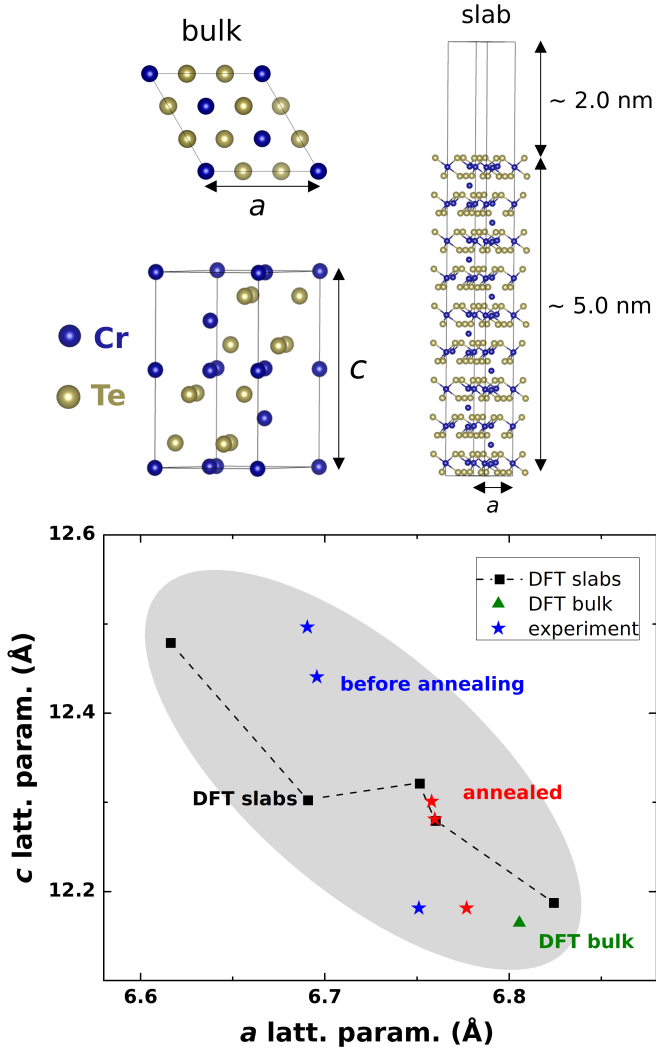


FIG. 4: Top: Cr_2Te_3 bulk crystal structure and a thin free-standing film constructed from it. The in-plane lattice parameter a was fixed at a range of values while the atomic positions were relaxed to obtain the out-of-plane lattice parameter c . Bottom: The calculated and experimental lattice parameters for free-standing slabs and for bulk structures. The measured values follow well the trend calculated for free-standing Cr_2Te_3 films.

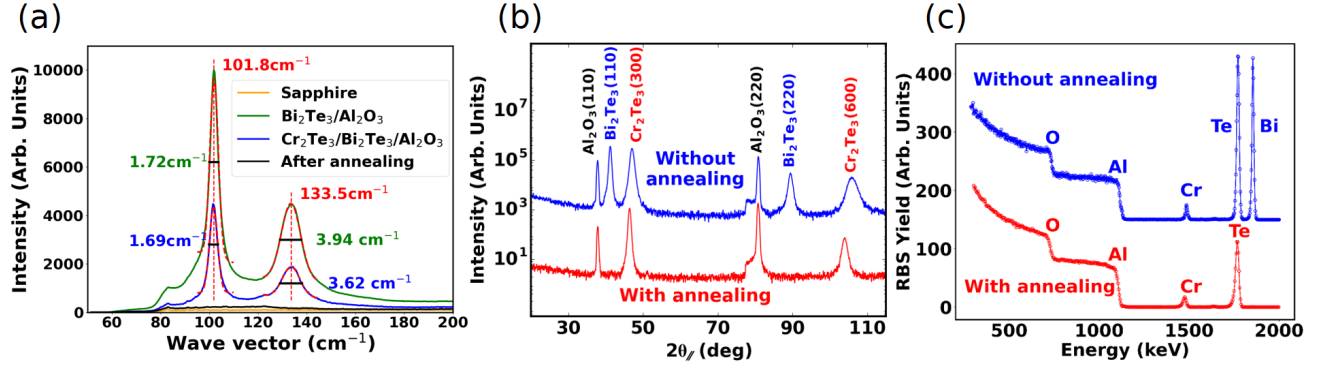


FIG. 5: Structural properties of Cr_2Te_3 on $\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$. (a) Raman spectra of the sapphire substrate, $\text{Bi}_2\text{Te}_3/\text{sapphire}$, and $\text{Cr}_2\text{Te}_3/\text{Bi}_2\text{Te}_3/\text{sapphire}$ with and without annealing. Positions and full widths at half maximum of Bi_2Te_3 peaks are indicated. (b) Radial x-ray diffraction spectra for $\text{Cr}_2\text{Te}_3/\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$ without (top in blue) and after (bottom in red) annealing. (c) RBS of Cr_2Te_3 grown on $\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$ without (top in blue) and with (bottom in red) annealing. No elemental Bi can be found after annealing.

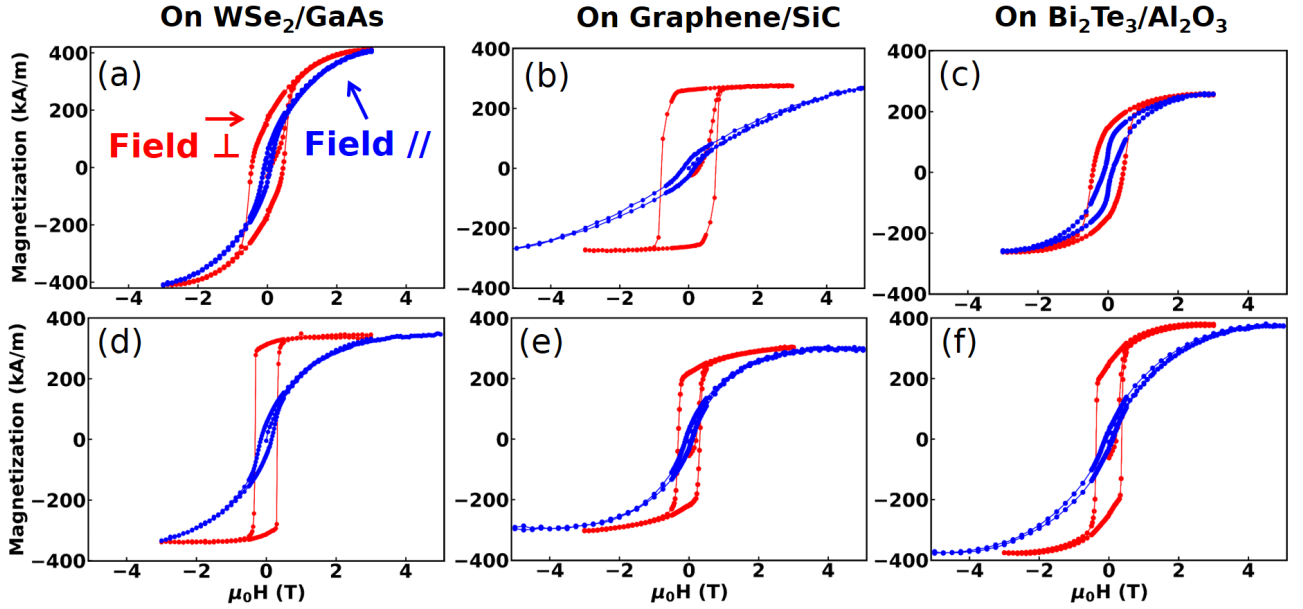


FIG. 6: SQUID hysteresis loops with out-of-plane (\perp) and in-plane (\parallel) applied magnetic field measured at 5 K are plotted after the removal of the substrate diamagnetic contribution. (a) (b) (c) Measurements on samples 1, 3 and 5 (without annealing on WSe_2/GaAs , $\text{graphene}/\text{SiC}$, and $\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$). (d) (e) (f) Same measurements on samples 2, 4 and 6 (annealed at 400°C).

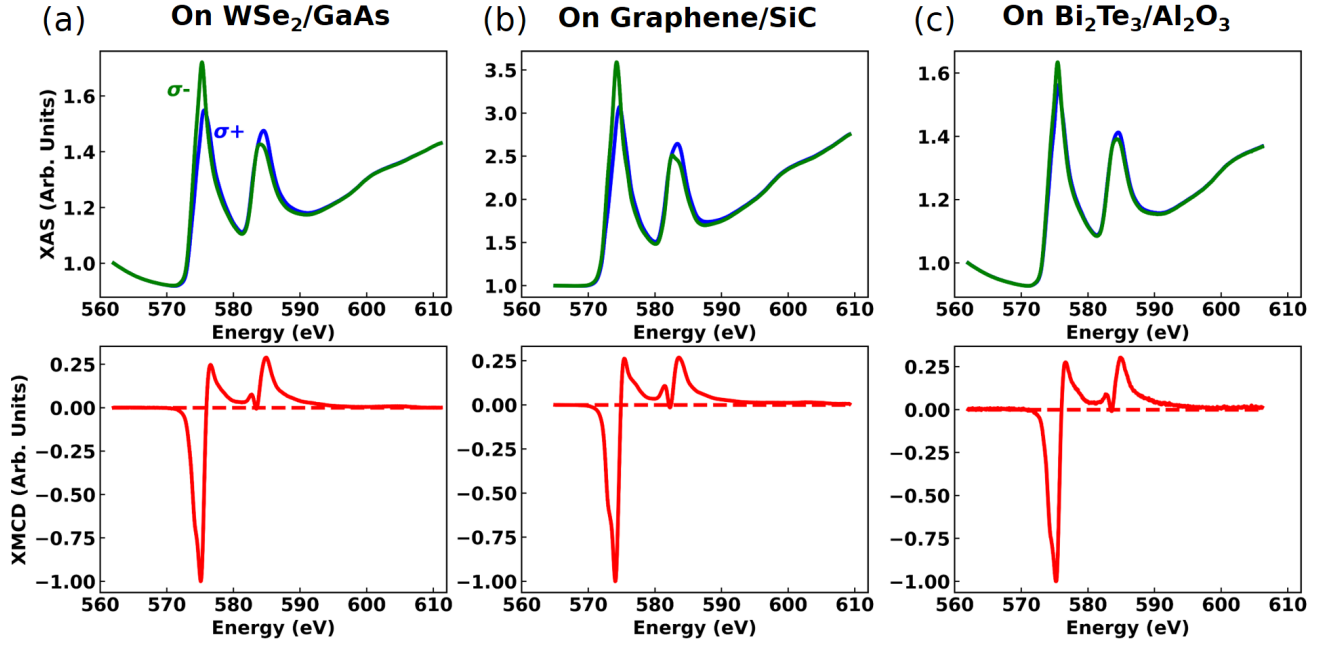


FIG. 7: Top: x-ray absorption spectroscopy (XAS) and bottom: x-ray magnetic circular dichroism (XMCD) measurements performed on Cr_2Te_3 layers grown and annealed on (a) WSe_2 (sample 2), (b) graphene (sample 4) and (c) Bi_2Te_3 (sample 6).

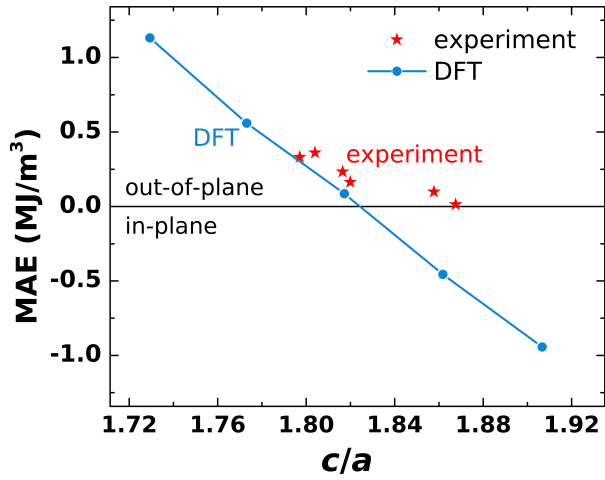


FIG. 8: Magnetic anisotropy energy of bulk Cr_2Te_3 as a function of strain compared for experiment and theory. It is a sum of the DFT-calculated magnetocrystalline energy with a demagnetizing energy contribution of -0.06 MJ/m^3 corresponding to the experimentally measured magnetization of $\approx 300 \text{ kA/m}$.

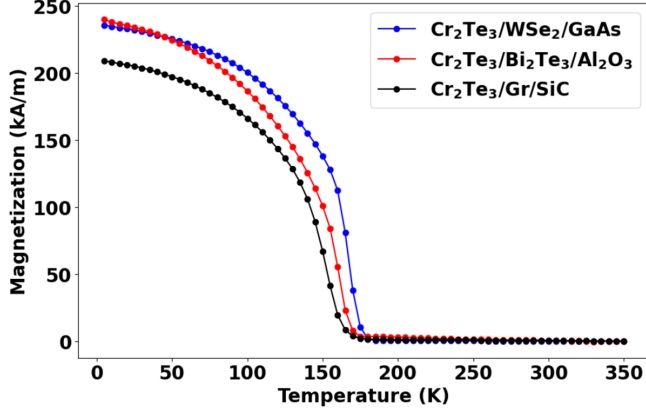


FIG. 9: Remanent magnetization of Cr_2Te_3 layers grown and annealed on WSe_2 (sample 2), graphene (sample 4), and Bi_2Te_3 (sample 6) as a function of temperature with no external field.

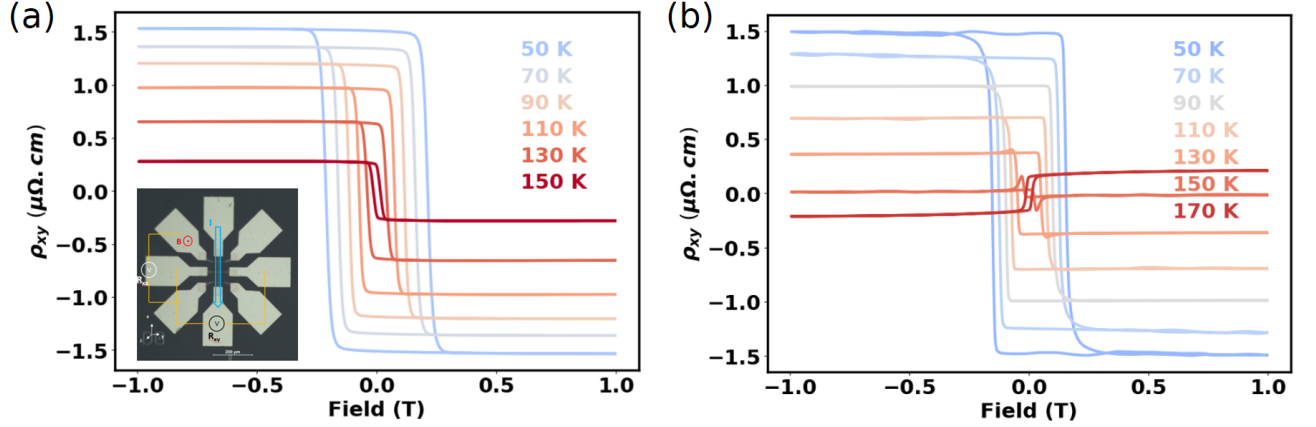


FIG. 10: (a) Temperature-dependent Hall resistivity of $\text{Cr}_2\text{Te}_3/\text{WSe}_2/\text{GaAs}$ (sample 2) after removal of the ordinary Hall slope with a magnetic field applied out-of-plane. Inset: an optical image of the Hall bar device processed by laser lithography with $\text{Ti}(10\text{nm})/\text{Au}(100\text{nm})$ contacts. (b) Temperature-dependent Hall resistivity of $\text{Cr}_2\text{Te}_3/\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$ (sample 6) after annealing (evaporation of Bi_2Te_3) and subtraction of the ordinary Hall slope.

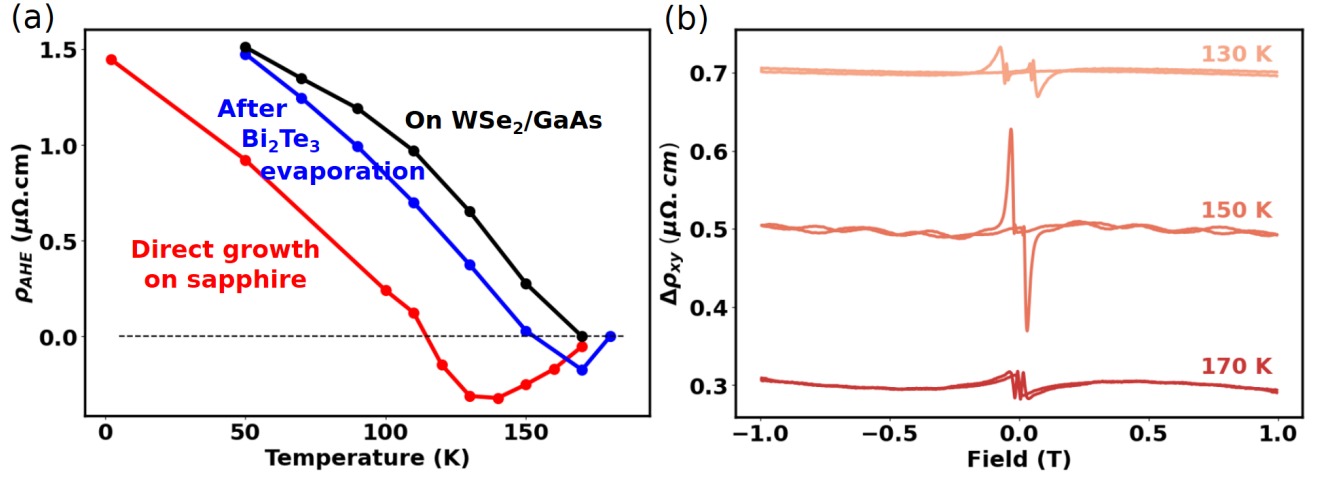


FIG. 11: (a) Anomalous Hall resistivity of $\text{Cr}_2\text{Te}_3/\text{Al}_2\text{O}_3$ as a function of temperature for direct growth on sapphire, after thermal removal of the Bi_2Te_3 layer and growth on WSe_2 . (b) Hall resistivity of Cr_2Te_3 deposited on Bi_2Te_3 and annealed after subtracting the ordinary and anomalous Hall contributions. The curves are vertically shifted for clarity.

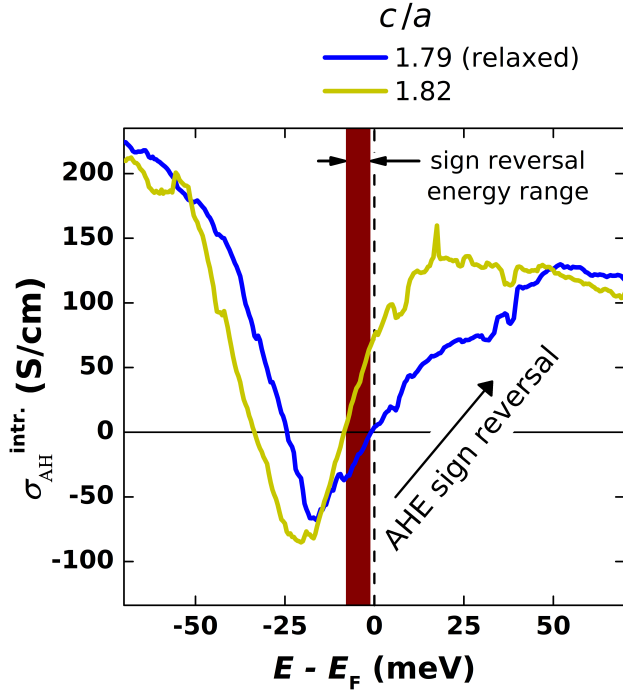


FIG. 12: Intrinsic Anomalous Hall conductivity in bulk Cr_2Te_3 as a function of energy. A sign reversal occurs close to E_{F} . Two different strains (c/a ratios) are considered, in agreement with the experimental ones.

Films with E_{F} within the red energy range will experience $\sigma_{\text{AH}}^{\text{intr.}}$ sign reversal upon this possible strain change with temperature.

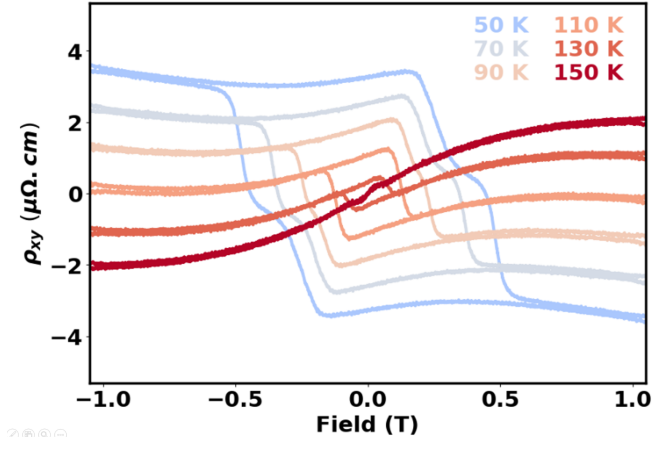


FIG. 13: Temperature-dependent Hall resistivity of $\text{Cr}_2\text{Te}_3/\text{graphene}/\text{SiC}$. An arbitrary slope of $4 \mu\Omega.\text{cm}/\text{T}$ has been subtracted for comparison with Fig. 10.

Supplemental Material: Epitaxial van der Waals heterostructures of Cr_2Te_3 on 2D materials

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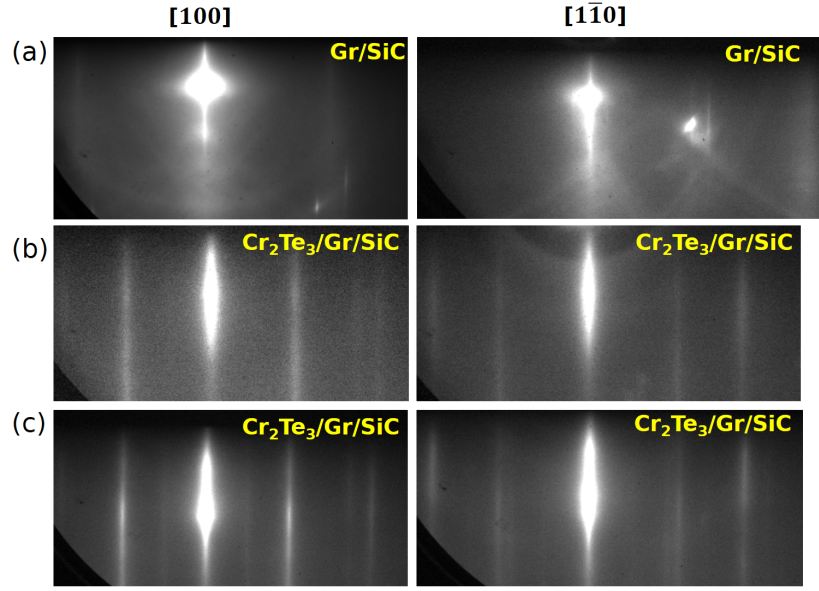
(Dated: March 7, 2023)

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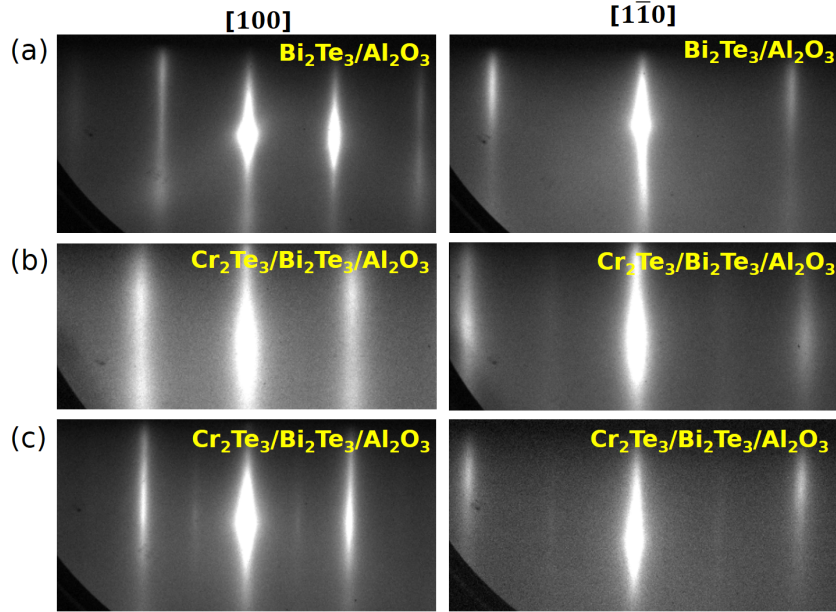
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* QG and LV contributed equally to this work

S1. RHEED IMAGES OF Cr_2Te_3 LAYERS ON GRAPHENE/SiC AND $\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$



(1) On Graphene/SiC



(2) On $\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$

FIG. S1: (a) In-situ RHEED images of the 2D material along two main crystal directions. (b) RHEED pattern after the deposition of Cr_2Te_3 at 300°C. (c) RHEED pattern after annealing at 400°C.

S2. LATTICE PARAMETER OF HETEROSTRUCTURES WITH INCREASING Cr_2Te_3 THICKNESS

We argue that the choice of a particular 2D material has a negligible effect on the Cr_2Te_3 /2D material lattice parameters. We support this by performing DFT relaxation of Cr_2Te_3 /graphene heterostructures with different Cr_2Te_3 thicknesses (see Fig. S2). A linear trend is observed. The value interpolates to the one of Cr_2Te_3 bulk at ≈ 7 MLs of Cr_2Te_3 , while the experimentally grown films have a thickness of 5 MLs. Hence, the lattice parameter of Cr_2Te_3 is expected to retain its bulk value. Even more when considering that in the calculation the two materials are bound to occupy the same unit cell. This makes their lattice parameters coupled more strongly than in reality.

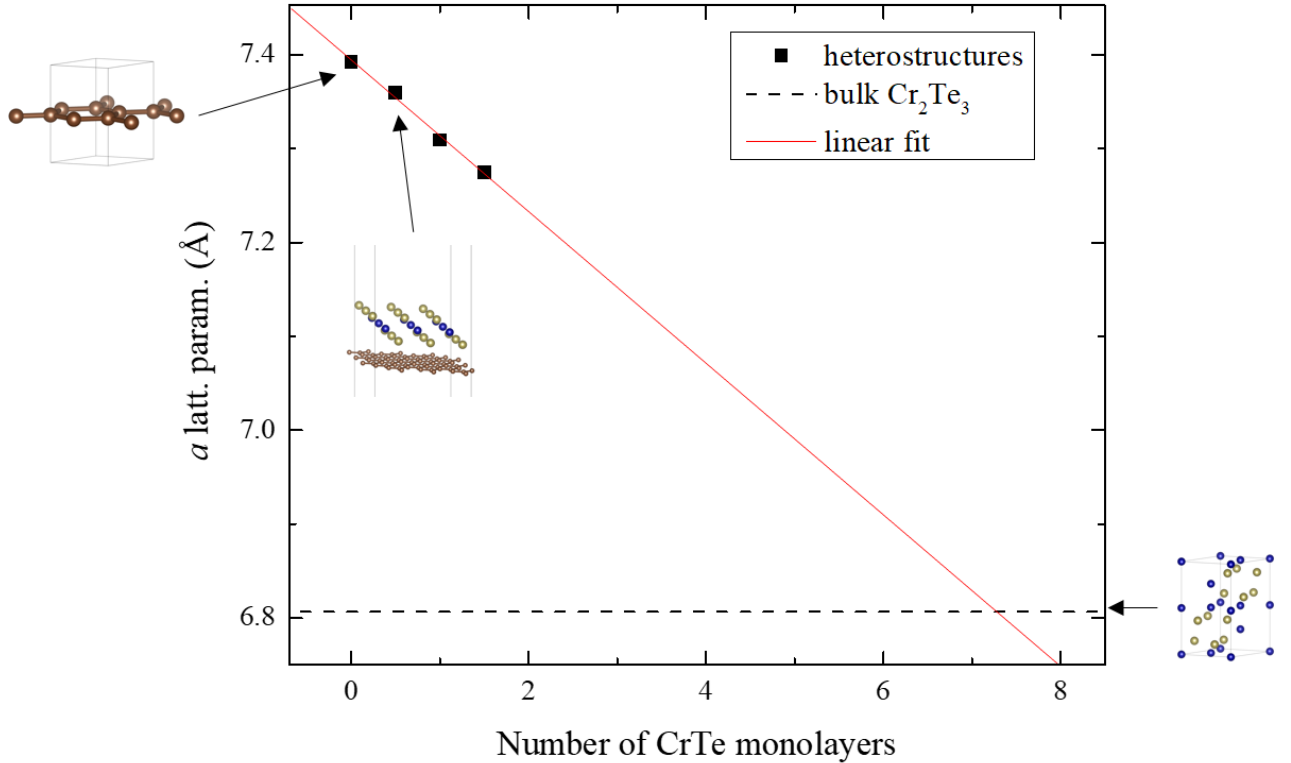


FIG. S2: The in-plane lattice parameter of Cr_2Te_3 /graphene heterostructure with increasing Cr_2Te_3 thickness.

S3. Cr_2Te_3 TERMINATION STABILITY

To build heterostructures made of Cr_2Te_3 and 2D materials, it is necessary to determine the stable termination of Cr_2Te_3 , as there are 4 distinct possible terminations (Fig. S3). It has been shown by Wen *et al.* [S1] that Cr_2Te_3 should be terminated by Te, with a complete CrTe_2 layer at the boundary. The same conclusion was reached by Lasek *et al.* [S2] performing molecular dynamics of differently terminated Cr_2Te_3 on MoS_2 . On the contrary, Bian *et al.* [S3] concluded that the intercalated Cr is the one that should lie at the interface, arguing that this leads to strain relaxation. Due to this discordance in the literature we performed our own surface stability calculations. Similar to [S1] we define the formation energy by:

$$F_{\text{form}} = (F_{\text{tot}} - n_{\text{Cr}}\mu_{\text{Cr}} - n_{\text{Te}}\mu_{\text{Te}})/N_{\text{atoms}} \quad (1)$$

where F_{tot} is the total calculated free energy, μ_i is the chemical potential and n_i is the number of atoms of element i in the unit cell, and N_{atoms} is the total number of atoms per unit cell. The chemical potential μ is taken either as the free energy of an isolated atom (Cr or Te) or the free energy per atom in the bulk of the given material. Both cases give the same qualitative result regarding the surface termination (see Table S1). From our calculations, we conclude that the Te-terminated surface is indeed the most stable (Table S1), although the formation energy of the intercalated Cr-terminated structure is very close - the difference is only 35 meV/atom (for μ from the Cr and Te bulk structures).

TABLE S1: Chemical potentials of Cr and Te atoms and bulk. The formation energy of 4 differently-terminated Cr_2Te_3 thin films in vacuum. The most stable is structure III, see Fig. S3 for its definition.

	μ (eV)		F_{tot} (eV)	n_{Cr}	n_{Te}	$F_{\text{form}}^{\text{atoms}}$ (eV)	$F_{\text{form}}^{\text{bulk}}$ (eV)
Cr atom	-4.89	structure I	-462.477	33	48	-3.318	-0.365
Te atom	-0.68	structure II	-474.406	35	48	-3.264	-0.305
Cr bulk	-8.10	structure III	-504.478	35	54	-3.336	-0.390
Te bulk	-3.45	structure IV	-483.289	33	54	-3.282	-0.342

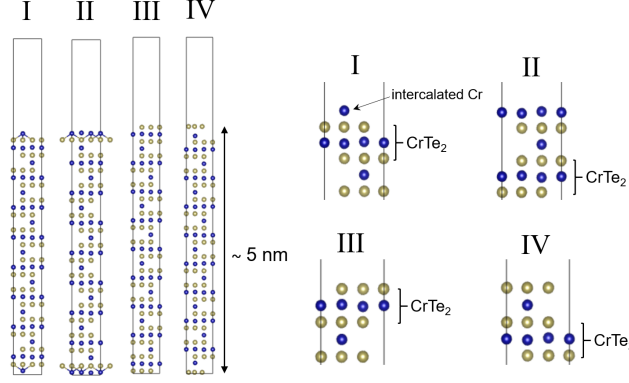


FIG. S3: Cr_2Te_3 thin films in vacuum used for the calculation of the surface-termination stability. Structure III (terminated by a complete CrTe_2 layer) is the most stable, followed by the intercalated Cr-terminated structure I. This corresponds to Ref. [S1].

S4. STOICHIOMETRY OF THE LAYERS

To verify the stoichiometry of the grown samples, Rutherford Back Scattering (RBS) was performed (see Fig. S4). The sample on graphene ($n^\circ 3$) was capped with amorphous Se and the one on Bi_2Te_3 (sample 5) was protected with Al. The ratio found is close to the expected 40% Cr and 60% Te.

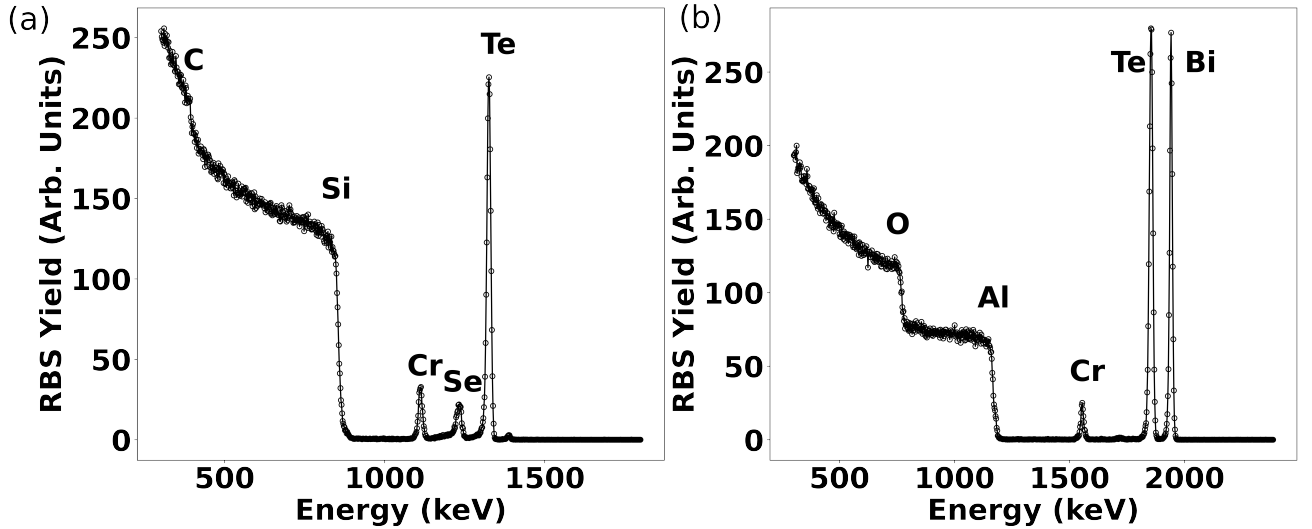


FIG. S4: Stoichiometry of Cr_xTe_3 (a) RBS of $\text{Cr}_{1.88}\text{Te}_3$ deposited on Gr/SiC (sample 3).

(b) RBS of $\text{Cr}_{1.97}\text{Te}_3$ grown on $\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$ (sample 5). The exact stoichiometry of Bi_2Te_3 was considered to deduce the Cr/Te ratio in Cr_2Te_3 .

S5. RAMAN SCATTERING OF MONOLAYER GRAPHENE

Raman scattering is used to control the graphene quality [S4]. We show in Fig. S5 that graphene is mostly unaffected by the deposition of Cr_2Te_3 .

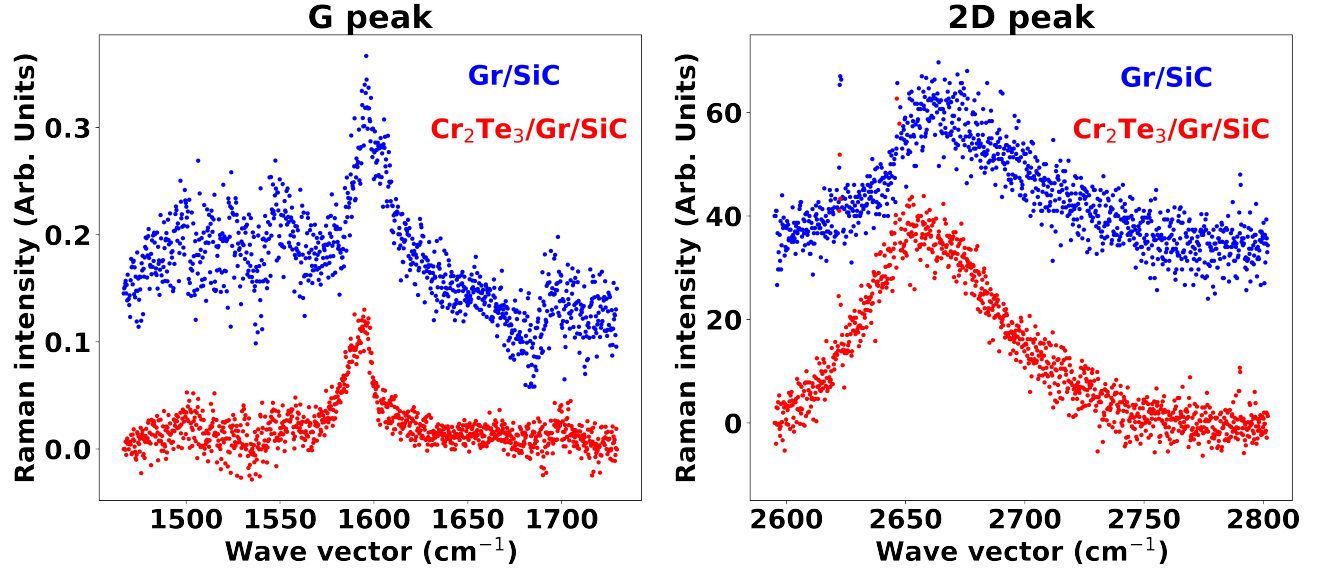


FIG. S5: Two characteristic Raman scattering peaks of monolayer graphene before and after deposition of Cr_2Te_3 .

S6. HYSTERESIS LOOP MEASURED BY XMCD

To confirm the origin of the magnetic signal in Cr_2Te_3 layers, we measured at the Soleil synchrotron source an hysteresis loop at the chromium L_3 edge and obtained a consistent signal with the experimental observations by SQUID magnetometry.

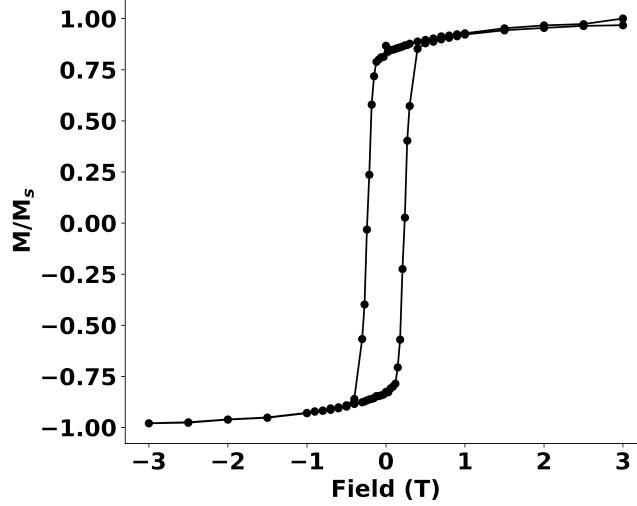


FIG. S6: Hysteresis loop of $\text{Cr}_2\text{Te}_3/\text{Graphene}/\text{SiC}$ measured at 5 K with a perpendicular applied magnetic field by recording the difference of XMCD signals at the chromium L_3 edge (corresponding to the maximum dichroic signal) and at 565 eV (pre-edge).

S7. LAYER-RESOLVED MAGNETIC MOMENTS IN 2D MATERIAL/ Cr_2Te_3 HETEROSTRUCTURES FROM *AB INITIO* CALCULATIONS

We simulate heterostructures of Cr_2Te_3 on Bi_2Te_3 , graphene, and WSe_2 , as well as Cr_2Te_3 slabs suspended in vacuum. None of these show a significant change of the interfacial magnetic moments in Cr_2Te_3 – all the Cr and Te atoms keep their magnetic moments of $\mu_{\text{Cr}} \approx 3.3 \mu_B$ and $\mu_{\text{Te}} \approx -0.3 \mu_B$, see Fig. S7.

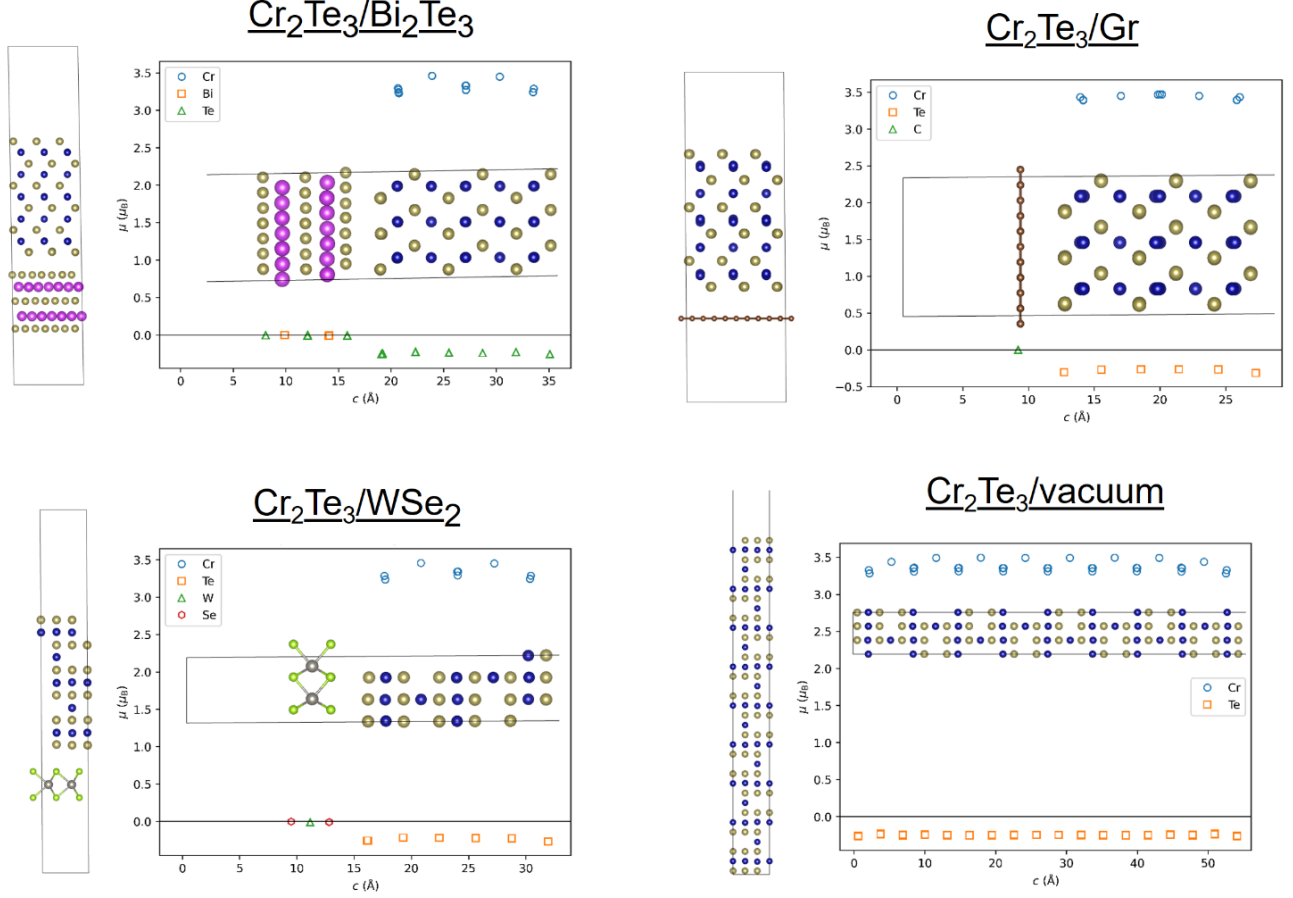


FIG. S7: Layer-resolved magnetic moments in *ab initio*-calculated Cr_2Te_3 /2D material heterostructures. The magnetic moments of the 2D materials are negligible. Moreover, we do not observe any significant modification of the Cr_2Te_3 magnetic moments at the interface.

S8. METALLIC RESISTIVITY OF Cr_2Te_3 LAYERS

The magnetoresistance of 5 layers Cr_2Te_3 deposited on the insulating substrate Al_2O_3 is shown in Fig. S8. The resistivity is growing with temperature indicating the metallic nature of Cr_2Te_3 layers. A change in the slope is noticeable around the Curie temperature of the material.

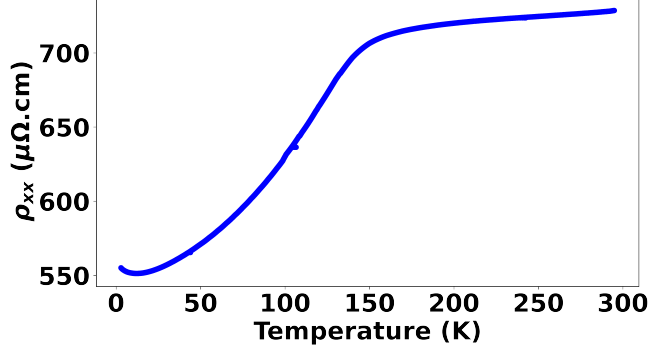


FIG. S8: Longitudinal resistivity of Cr_2Te_3 deposited on sapphire versus temperature.

S9. HALL RESISTIVITY OF Cr_2Te_3 ON SAPPHIRE

To understand the Hall signal measured on $\text{Cr}_2\text{Te}_3/\text{Bi}_2\text{Te}_3/\text{Al}_2\text{O}_3$ annealed at 400°C (when the Bi_2Te_3 layer evaporated), Cr_2Te_3 was directly deposited on sapphire and measured (see Fig. S9). The extracted carrier density was found higher (7.0×10^{15} holes/ cm^2 at 50 K) and a similar sign change of the anomalous Hall resistivity is noticeable below the Curie temperature. The temperature at which the resistivity switches sign occurs below the sample deposited on Bi_2Te_3 . This difference is attributed to the presence of defects after removal of Bi_2Te_3 and therefore to different Fermi levels in these two samples.

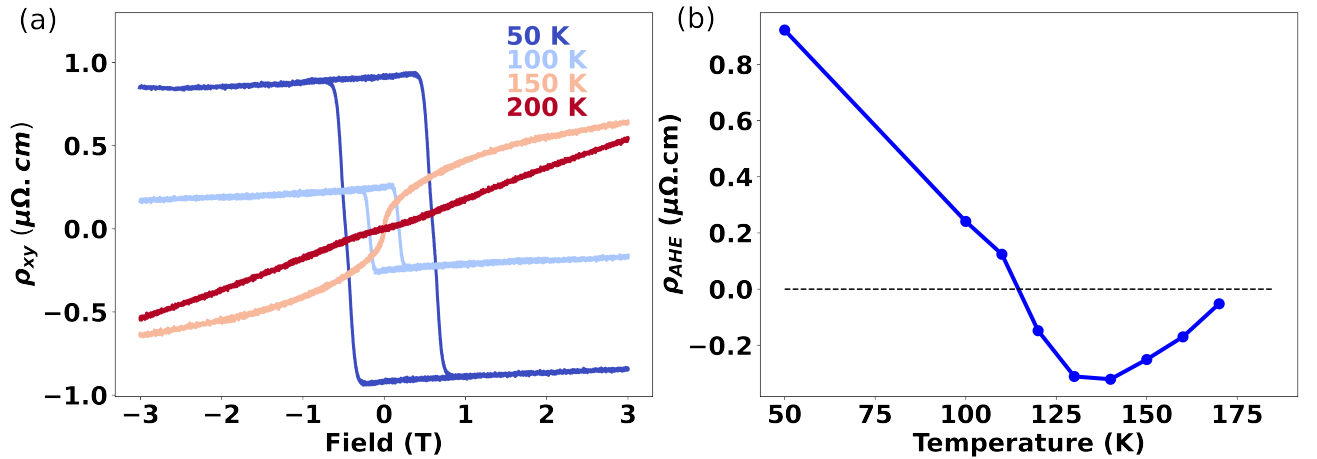


FIG. S9: (a) Hall resistivity of Cr_2Te_3 deposited on sapphire at different temperatures. (b) Extracted anomalous Hall resistivity as a function of temperature.

S10. ANOMALOUS HALL EFFECT SIGN REVERSAL

The anomalous Hall effect sign reversal around the Fermi level is sensitive to strain [Fig. S10(a)], but not to volume expansion [Fig. S10(d)]. The strain can significantly change both the value of $\sigma_{\text{AH}}^{\text{intr.}}$ at E_{F} [Fig. S10(b)] and the Fermi level position at which the sign reversal occurs [Fig. S10(c)]. In comparison, a realistic thermal volume expansion (0.5% per 300K [S5]) does not change the $\sigma_{\text{AH}}^{\text{intr.}}$ curve characteristics significantly [Fig. S10(e)-(f)].

Note that an equivalent calculation in Ref. [S6] does not show the reversal around E_{F} . We could reproduce this result by neglecting the vdW correction. The vdW correction is, however, important, due to the presence of the pseudo vdW gap in Cr_2Te_3 . Otherwise, the relaxed unit cell volume is overestimated (by $\approx 8\%$) compared to both experiment and the calculation with vdW correction included.

A reversal is still present in Ref. [S6], but at $E - E_{\text{F}} = 300$ meV. We performed a charge transfer calculation and show that a charge transfer from the 2D materials to Cr_2Te_3 should indeed increase its Fermi level, but only by 25 meV at most. Therefore a sign reversal region around 300 meV seems unrealistic.

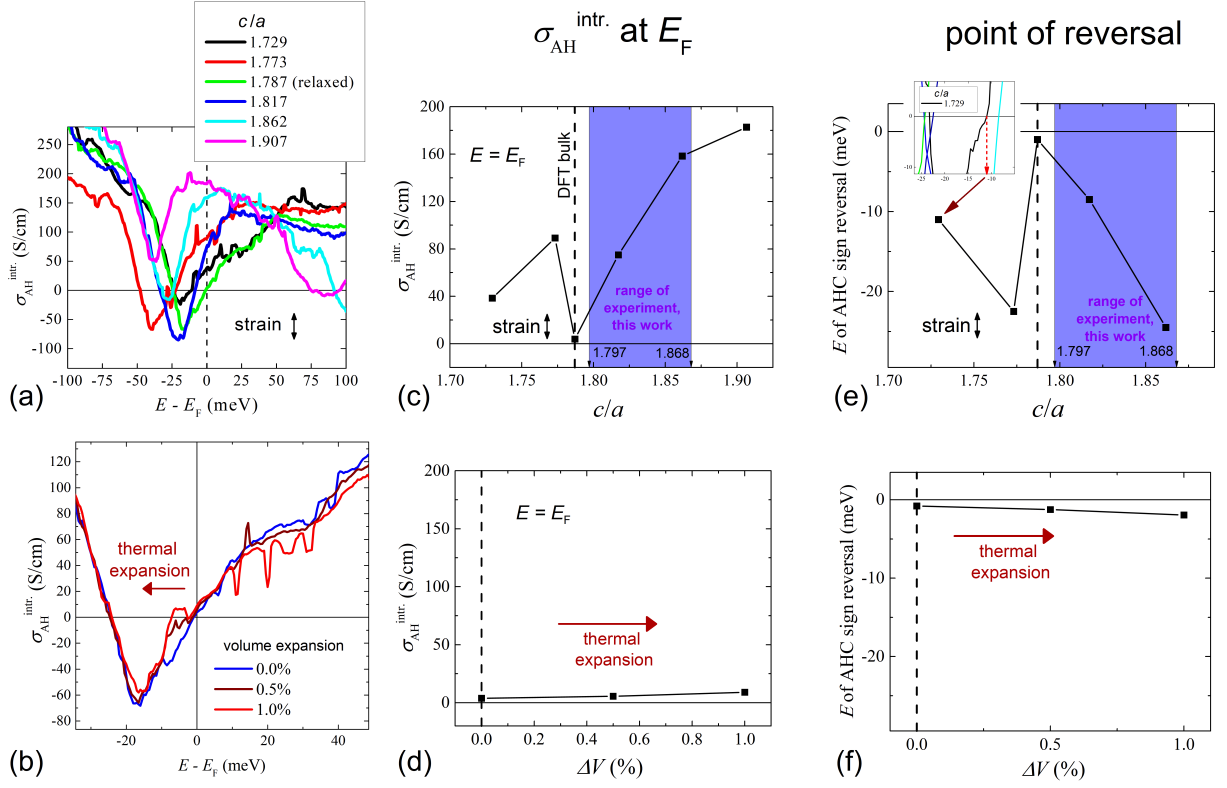


FIG. S10: (a) The intrinsic AHC $\sigma_{\text{AH}}^{\text{intr.}}$ as a function of the Fermi level position for bulk Cr_2Te_3 under strain and (b) volume expansion. The strain can have a significant effect on AHC. (c) $\sigma_{\text{AH}}^{\text{intr.}}$ at the Fermi level as a function of strain and (d) volume expansion. (e) Shift of the (right-most) sign reversal energy as a function of strain and (f) volume expansion.

S11. CHARGE TRANSFER BETWEEN Cr_2Te_3 AND 2D MATERIALS

We calculate heterostructures of Cr_2Te_3 /2D materials to estimate the charge transfer between the studied 2D materials and Cr_2Te_3 (see Fig. S11). We observe a positive electron transfer to Cr_2Te_3 in all three cases. The resulting shift of the Cr_2Te_3 Fermi level compared to its bulk value is estimated by dividing the number of transferred electrons/unit cell by the density of states of bulk Cr_2Te_3 at E_F , in this case, 8.05 electrons/eV for the considered unit cell.

In the case of graphene, the charge transfer is one order of magnitude larger than for WSe_2 or Bi_2Te_3 , leading to an estimated $\Delta E_F \approx 54$ meV.

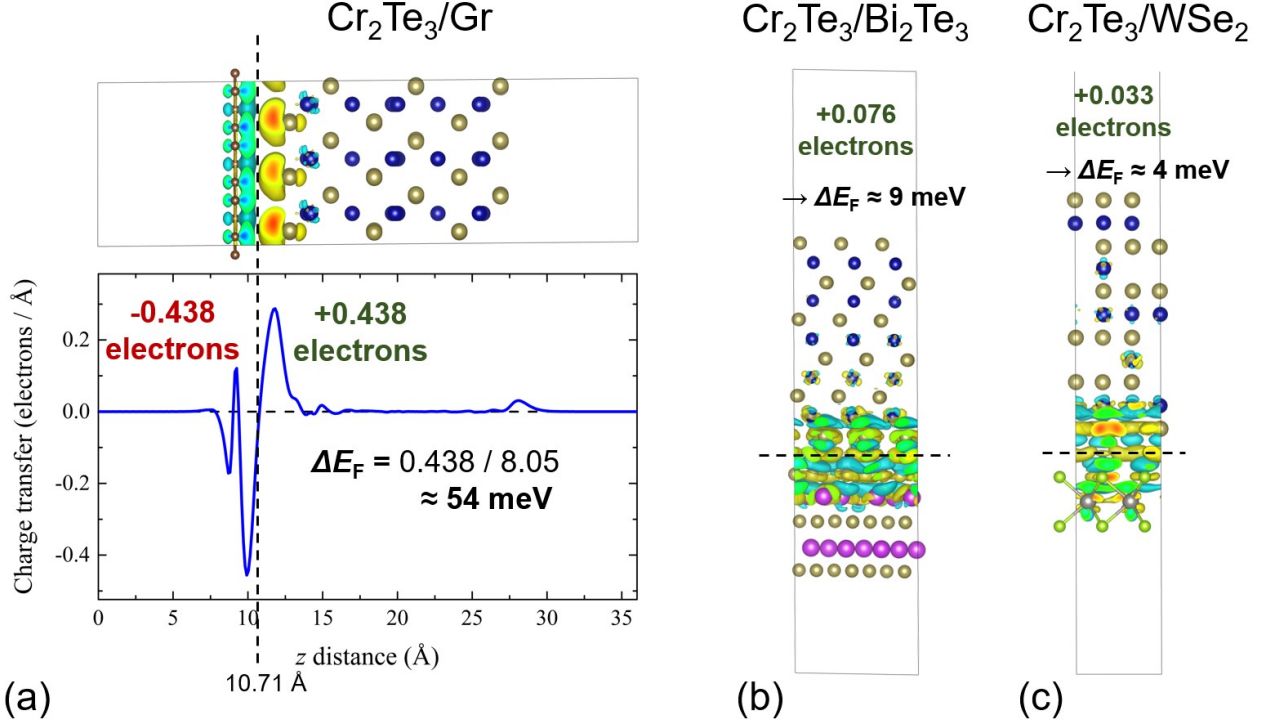


FIG. S11: Charge transfer calculation for Cr_2Te_3 on top of (a) graphene, (b) Bi_2Te_3 , and (c) WSe_2 . Yellow cloud signifies positive and blue signifies negative electron transfer. In green is given the number of electrons (per unit cell) transferred from the 2D material to Cr_2Te_3 . An estimation of the Fermi level shift ΔE_F compared to bulk Cr_2Te_3 resulting from this charge transfer is also given.

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